

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,806,095 B2  
APPLICATION NO. : 10/092795  
DATED : October 19, 2004  
INVENTOR(S) : Nallan et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the Title page, in field (56), under "Foreign Patent Documents", in column 2, line1, after "12/2001" insert -- H01L --.

In column 1, line 46, delete "HfO2, ZrO2" and insert -- HfO<sub>2</sub>, ZrO<sub>2</sub> --, therefor.

In column 1, line 47, delete "HfSiO<sub>2</sub>" and insert -- HfSiO<sub>2</sub>--, therefor.

In column 1, line 53, delete "CL<sub>2</sub>/CO" and insert -- Cl<sub>2</sub>/CO --, therefor.

In columns 3-4, lines 66-67 and 1-2, below "The foregoing steps of the.....dielectric layer." delete "The foregoing steps of the.....dielectric layer."

(Repeated occurrence)

In column 4, line 40, delete "3500° C" and insert -- 350° C--, therefor.

In column 4, line 64, delete "hafniumoxide" and insert -- hafnium-oxide --, therefor.

In column 6, line 10, in Claim 11, delete "A" before "The".

In column 6, line 16, in Claim 12, after "material" insert -- , --.

In column 6, line 39, in Claim 17, after "gas;" insert -- and --.

Signed and Sealed this

Twenty-sixth Day of December, 2006



JON W. DUDAS

*Director of the United States Patent and Trademark Office*